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Advances in Silicon Carbide Processing and Applications ...

Advances in Silicon Carbide Processing and Applications. Stephen E. Saddow, Anant K. Agarwal. Artech House, 2004 - Science - 212 pages. 1 Review. Learn the latest advances in SiC (Silicon Carbide)...

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Advances in Silicon Carbide Processing and Applications ...

Abstract Since the production of the first commercially available blue LED in the late 1980s, silicon carbide technology has grown into a billion-dollar industry world-wide in the area of...

(PDF) Advanced Silicon Carbide and Processing

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Advances in silicon carbide processing and applications [electronic resource] / Stephen E. Saddow, Anant Agarwal, editors. Corporate Author: Ebook Central Academic Complete., ProQuest (Firm) Other authors: Saddow, Stephen E. Agarwal, Anant: Format: eBook Online access: Connect to electronic book via Ebook Central.

Staff view: Advances in silicon carbide processing and ...

Silicon carbide is a promising semiconductor for advanced power devices that can outperform Si devices in extreme environments (high power, high temperature, and high frequency). In this article, we discuss recent progress in the development of passivation techniques for the SiO 2 /4H-SiC interface critical to the development of SiC metal oxide semiconductor field-effect transistor (MOSFET) technology.

MRS Bulletin: Volume 30 - Advances in Silicon Carbide ...

While this is an excellent means to convey important aspects of the technol- ogy, the intent of Advances in Silicon Carbide Processing and Applications is to be less expansive and focus in on two of the most promising applications of SiC tech- nology: gas and chemical sensing and electric vehicle motor drive and control.

S.e.saddow, a.agarwal advances in silicon carbide ...

advances in silicon carbide processing and applications semiconductor materials and devices series By Stan and Jan Berenstain FILE ID 6598e7 Freemium Media Library Advances In Silicon Carbide Processing And Applications Semiconductor Materials And Devices Series PAGE #1 : Advances In Silicon Carbide Processing And Applications Semiconductor ...

Learn the latest advances in SiC (Silicon Carbide) technology from the leading experts in the field with this new cutting-edge resource. The book is your single source for in-depth information on both SiC device fabrication and system-level applications. This comprehensive reference begins with an examination of how SiC is grown and how defects in SiC growth can affect working devices. Key issues in selective doping of SiC via ion implantation are covered with special focus on implant conditions and electrical activation of implants. SiC applications discussed include chemical sensors, motor-control components, high-temperature gas sensors, and high-temperature electronics. By cutting through the arcane data and jargon surrounding the hype on SiC, this book gives an honest assessment of today's SiC technology and shows you how SiC can be adopted in developing tomorrow's applications.

Since the 1997 publication of "Silicon Carbide - A Review of Fundamental Questions and Applications to Current Device Technology" edited by Choyke, et al., there has been impressive progress in both the fundamental and developmental aspects of the SiC field. So there is a growing need to update the scientific community on the important events in research and development since then. The editors have again gathered an outstanding team of the world's leading SiC researchers and design engineers to write on the most recent developments in SiC.

Silicon carbide (SiC) is a wide-bandgap semiconductor that can operate at temperatures well above 300 º C, where silicon cannot perform. In addition, due to a high thermal conductivity equal to copper at room temperature, SiC is an ideal candidate for operation in harsh environments and at high-power levels. Rapid advances in SiC materials and devices have recently resulted in implementation of SiC-based electronic systems, and the impact of these devices is expected to significantly increase in the next several years. This book documents the most recent results on growth of bulk and epitaxial layers, physical and structural properties, process technology, and device development obtained since the 10th International Conference on Silicon Carbide and Related Materials 2003 (ICSCRM2003) held in Lyon, France. Extended defects in silicon carbide are highlighted. The nature of defects induced by forward biasing of bipolar devices, as well as methods to suppress the degradation, are addressed.

Symposium K is the second in a series of SiC symposia at the MRS Fall Meeting. Since the last meeting in 2000, advances in SiC materials, processing, and device design have resulted in implementation of SiC-based electronic systems and offer great promise in high voltage, high temperature, high frequency applications. Presenters focused on new developments in the basic science of SiC materials as well as rapidly maturing device technologies. The challenges in this field include understanding and decreasing defect densities in bulk SiC crystals, controlling morphology and residual impurities in epilayers, optimization of implant activation and oxide-SiC interfaces, and developing novel device structures. Topics of particular interest were in the area of bulk SiC growth (including large-diameter crystals), modeling, characterization, homo- and heteroepitaxial growth (e.g., doping control, morphology development, and carrier lifetimes), advances in ion implantation, improved ohmic and rectifying contacts, surfaces and interfaces, oxidation, and alternative dielectric materials and devices (including high-voltage, high-temperature, high-frequency sensors and system level benefits).

Advances in silicon carbide materials, processing and device design have recently resulted in implementation of SiC-based electronic systems and offer great promise in high-voltage, high-temperature and high-frequency applications. This volume focuses on new developments in basic science of SiC materials as well as rapidly maturing device technologies. The challenges in this field include understanding and decreasing defect densities in bulk SiC crystals, controlling morphology and residual impurities in epilayers, optimization of implant activation and oxide-SiC interfaces, and developing novel device structures. This book brings together the crystal growers, physicists and device experts needed to continue the rapid pace of silicon-carbide-based technology. Topics include: epitaxial growth; characterization/defects; MOS technology; SiC processing and devices.

Advances in Ceramic Matrix Composites, Second Edition, delivers an innovative approach to ceramic matrix composites, focusing on the latest advances and materials developments. As advanced ceramics and composite materials are increasingly utilized as components in batteries, fuel cells, sensors, high-temperature electronics, membranes and high-end biomedical devices, and in seals, valves, implants, and high-temperature and wear components, this book explores the substantial progress in new applications. Users will gain knowledge of the latest advances in CMCs, with an update on the role of ceramics in the fabrication of Solid Oxide Fuel Cells for energy generation, and on natural fiber-reinforced eco-friendly geopolymer and cement composites. The specialized information contained in this book will be highly valuable to researchers and graduate students in ceramic science, engineering and ceramic composites technology, and engineers and scientists in the aerospace, energy, building and construction, biomedical and automotive industries. Provides detailed coverage of parts and processing, properties and applications Includes new developments in the field, such as natural fiber-reinforced composites and the use of CMCs in Solid Oxide Fuel Cells (SOFCs) Presents state-of-the-art research, enabling the reader to understand the latest applications for CMCs

This transactions volume contains 33 papers from the CREST International Symposium on SiC/SiC Composite Materials Research and Development and Its Application to Advanced Energy Systems held May 20-22, 2002 in Kyoto, Japan. Chapters include Processing for SiC/SiC Composites; Processing for SiC/SiC Composite Constituent; Characterization of Thermomechanical Performance; and Joining Technologies for Advanced Energy Applications. 373 pages.

Advances in silicon carbide materials, processing and device design have recently resulted in implementation of SiC-based electronic systems and offer great promise in high-voltage, high-temperature and high-frequency applications. This volume focuses on new developments in basic science of SiC materials as well as rapidly maturing device technologies. The challenges in this field include understanding and decreasing defect densities in bulk SiC crystals, controlling morphology and residual impurities in epilayers, optimization of implant activation and oxide-SiC interfaces, and developing novel device structures. This volume brings together the crystal growers, physicists and device experts needed to continue the rapid pace of silicon-carbide-based technology. Topics include: SiC bulk growth; SiC epitaxy; SiO2/SiC interfaces; SiC devices; SiC materials, characterization and devices; implantation/radiation damage; and metallization/characterization.

Silicon Carbide Biotechnology: A Biocompatible Semiconductor for Advanced Biomedical Devices and Applications, Second Edition, provides the latest information on this wide-band-gap semiconductor material that the body does not reject as a foreign (i.e., not organic) material and its potential to further advance biomedical applications. SiC devices offer high power densities and low energy losses, enabling lighter, more compact, and higher efficiency products for biocompatible and long-term in vivo applications, including heart stent coatings, bone implant scaffolds, neurological implants and sensors, glucose sensors, brain-machine-interface devices, smart bone implants, and organ implants. This book provides the materials and biomedical engineering communities with a seminal reference book on SiC for developing technology, and is a resource for practitioners eager to identify and implement advanced engineering solutions to their everyday medical problems for which they currently lack long-term, cost-effective solutions. Discusses the properties, processing, characterization, and application of silicon carbide biomedical materials and related technology Assesses literature, patents, and FDA approvals for clinical trials, enabling rapid assimilation of data from current disparate sources and promoting the transition from technology R&D, to clinical trials Includes more on applications and devices, such as SiC nanowires, biofunctionalized devices, micro-electrode arrays, heart stent/cardiovascular coatings, and continuous glucose sensors, in this new edition

The rapidly advancing Silicon Carbide technology has a great potential in high temperature and high frequency electronics. High thermal stability and outstanding chemical inertness make SiC an excellent material for high-power, low-loss semiconductor devices. The present volume presents the state of the art of SiC device fabrication and characterization. Topics covered include: SiC surface cleaning and etching techniques; electrical characterization methods and processing of ohmic contacts to silicon carbide; analysis of contact resistivity dependence on material properties; limitations and accuracy of contact resistivity measurements; ohmic contact fabrication and test structure design; overview of different metallization schemes and processing technologies; thermal stability of ohmic contacts to SiC, their protection and compatibility with device processing; Schottky contacts to SiC; Schottky barrier formation; Schottky barrier inhomogeneity in SiC materials; technology and design of 4H-SiC Schottky and Junction Barrier Schottky diodes; Si/SiC heterojunction diodes; applications of SiC Schottky diodes in power electronics and temperature/light sensors; high power SiC unipolar and bipolar switching devices; different types of SiC devices including material and technology constraints on device performance; applications in the area of metal contacts to silicon carbide; status and prospects of SiC power devices.